

SEMICONDUCTOR

# **BCW89**

## **PNP General Purpose Amplifier**

- This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Base 2. Emitter 3. Collector

## Absolute Maximum Ratings \* T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Value	Units
CEO	Collector-Emitter Voltage		-60	V
CES	Collector-Emitter Voltage		-60	V
ево	Emitter-Base Voltage		-5.0	V
0	Collector current	- Continuous	-500	mA
J, T <sub>stg</sub>	Junction and Storage Temperature		-55 ~ +150	°C

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

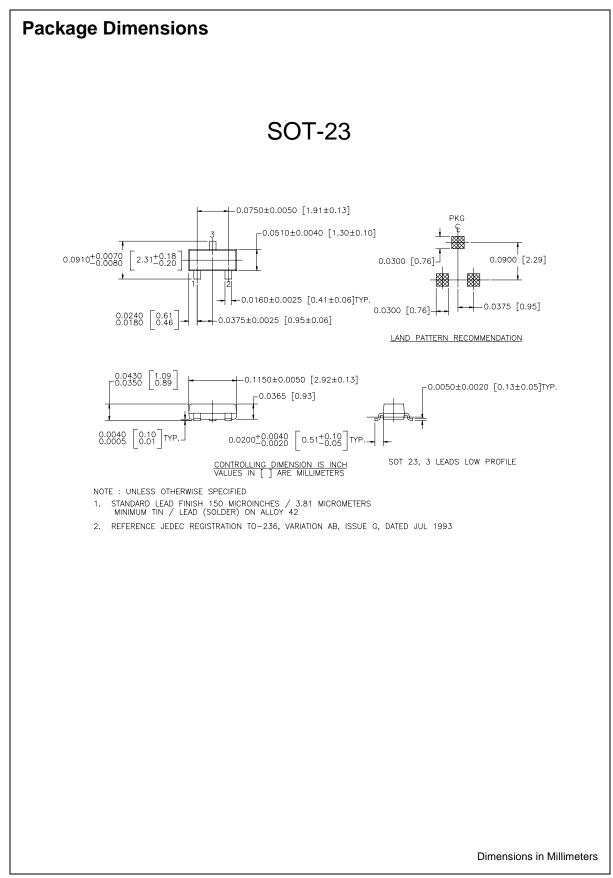
# Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units			
Off Charac	Off Characteristics							
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-80		V			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = -2.0 {\rm mA}, I_{\rm B} = 0$	-60		V			
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-60		V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm C} = -10\mu A, I_{\rm C} = 0$	-5.0		V			
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -20V, I_E = 0$ $V_{CB} = -20V, I_E = 0, T_A = +100^{\circ}C$		-100 -10	nA μA			
On Charac	teristics							
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5.0V, I_{C} = -2.0mA$	120	260				
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA		-0.3	V			
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$V_{CE} = -5.0V, I_{C} = -2.0mA$	-0.6	-0.75	V			
	al Characteristics							
NF	Noise Figure	$V_{CE} = -5.0V, I_C = -200\mu A$ $R_S = 2.0k\Omega, f = 1.0kHz$ $B_W = 200Hz$		10	dB			

# Thermal Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

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